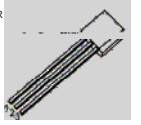


● Amplifier dissipation NPN Silicon

1. COLLECTOR
2. BASE
3. EMITTER



	Collector-Emitter Voltage	BC237	45	V
		BC238/239	25	
	Emitter-Base Voltage	BC237	6	V
		BC238/239	5	
	Collector Current -Continuous		0.1	A
	Collector Power Dissipation		350	mW
	Thermal Resistance, Junction to Ambient		357	/W
	Thermal Resistance, Junction to Case		125	/W
	Junction Temperature		150	
	Storage Temperature		-55d150	

T_a=25 °C unless otherwise specified

			in	yp	Max	nit
	V _{(BR)CBO}	I _C =100 A, I _E =0 BC237 BC238/239	50 30			V
	V _{(BR)CEO}	I _C =2mA, I _B =0 BC237 BC238/239	45 25			V
	V _{(BR)EBO}	I _E =100 A, I _C =0 BC237 BC238/239	6 5			V
	I _{CBO}	V _{CE} =50V, V _{BE} =0 V _{CB} =30V, I _E =0 BC237 BC238/239			15	nA
	h _{FE(1)}	V _{CE} =5V, I _C =10 A BC237A BC237B/238B BC237C/238C/239C		90 150 270		
	h _{FE(2)}	V _{CE} =5V, I _C =2mA BC237 BC239 BC237A BC237B/238B BC237C/238C/239C	120 120 120 200 380		800 800 220 460 800	
	h _{FE(3)}	V _{CE} =5V, I _C =100mA BC237A BC237B/238B BC237C/238C/239C		120 180 300		
	V _{CE(sat)}	I _C =10mA, I _B =0.5mA I _C =100mA, I _B =5mA BC237/238/239 BC237/239 BC238			0.2 0.6 0.8	V
	V _{BE(sat)}	I _C =10mA, I _B =0.5mA I _C =100mA, I _B =5mA			0.83 1.05	V
	V _{BE}	V _{CE} =5V, I _C =0.1mA V _{CE} =5V, I _C =2mA V _{CE} =5V, I _C =100mA	0.55	0.5 0.83	0.7	V
	f _T	V _{CE} =3V, I _C =0.5mA, f=100MHz BC237 BC238 BC239 V _{CE} =5V, I _C =10mA, f=100MHz BC237 BC238 BC239	150 150 150	100 120 140 200 240 280		MHz
	C _{ob}	V _{CB} =10V, I _E =0, f=1MHz			4.5	pF
	C _{ib}	V _{EB} =0.5V, I _C =0, f=1MHz		8		Pf
	NF	V _{CE} =5V, I _C =0.2mA, f=1kHz, R _s =2K BC239 V _{CE} =5V, I _C =0.2mA, f=1kHz, R _s =2K , f=200Hz BC237 BC238 BC239		2 2 2	4 10 10 4	dB